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SCD2160



Power Rectifier Diodes

Features

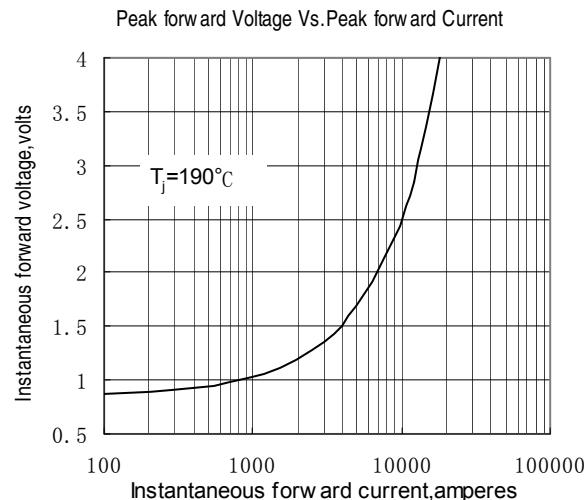
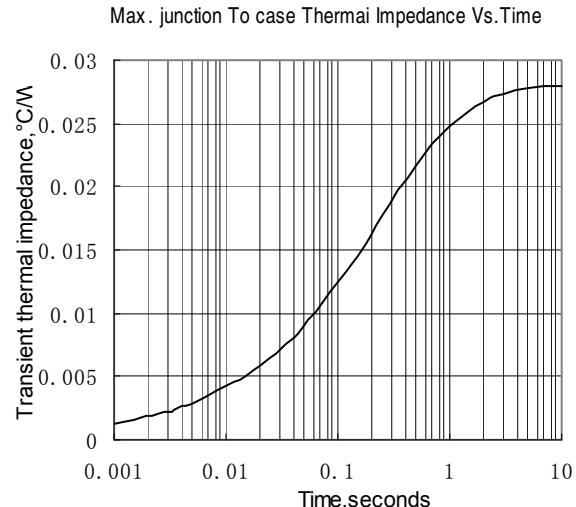
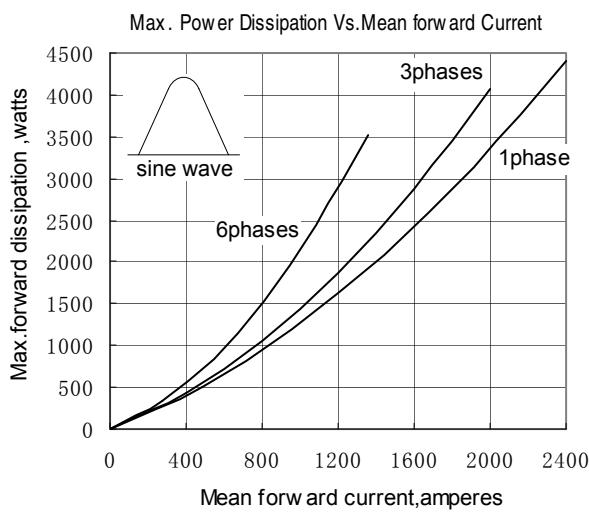
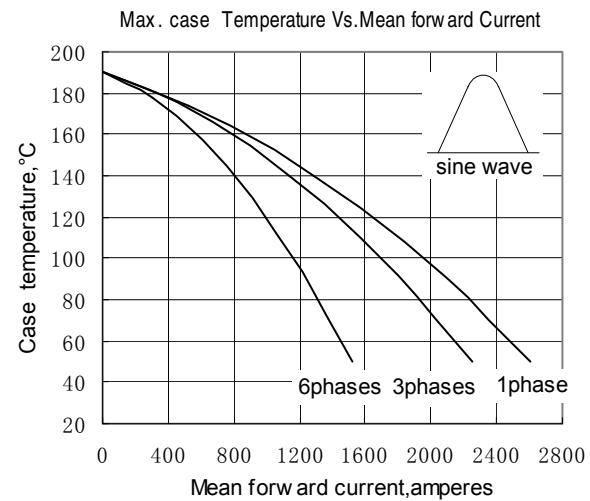
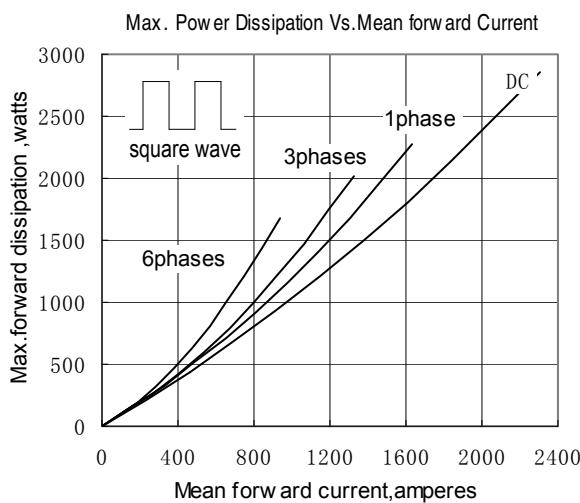
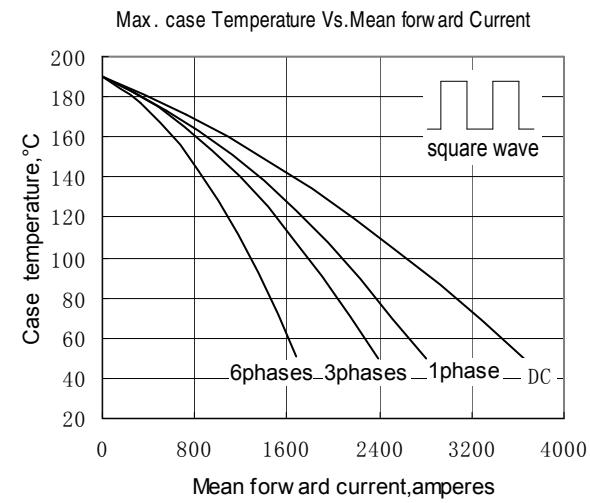
- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

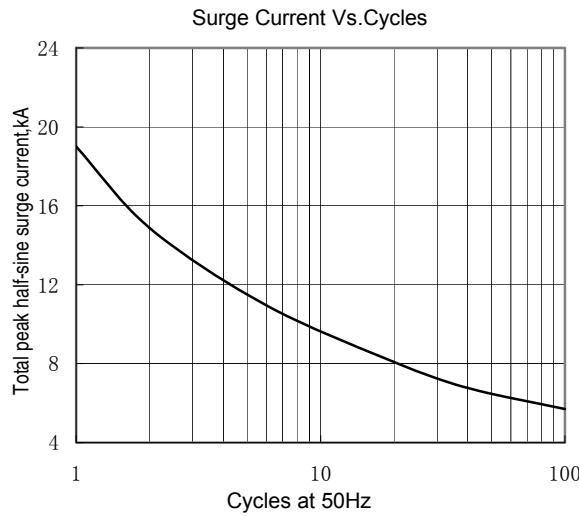
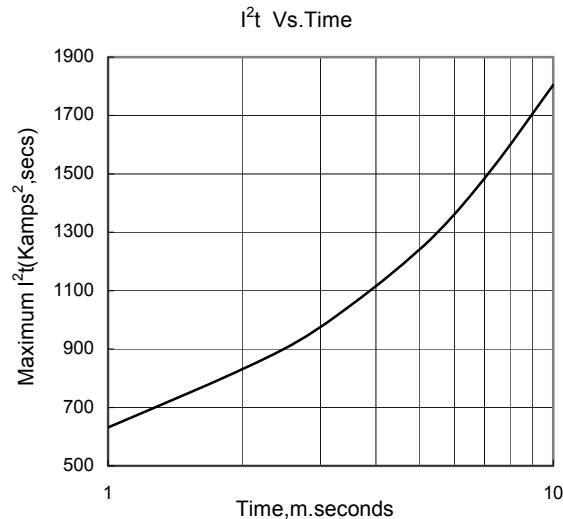
Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable rectifiers
- Controlled rectifiers

I_{F(AV)}	2160 A
V_{RRM}	200~1600 V
I_{FSM}	19 kA
I²t	1805 10³A²S

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Double side cooled,	190			2550	A
						2160	
V _{RRM}	Repetitive peak reverse voltage	V _{RRM} tp=10ms V _{RSM} = V _{RRM} +100V	190	200		1600	V
I _{RRM}	Repetitive peak current	V _{RM} = V _{RRM}	190			50	mA
I _{FSM}	Surge forward current	10ms half sine wave V _R =0.6V _{RRM}	190			19	kA
I ² t	I ² T for fusing coordination					1805	A ² s*10 ³
V _{FO}	Threshold voltage		190			0.86	V
r _F	Forward slop resistance					0.165	mΩ
V _{FM}	Peak on-state voltage	I _{FM} =3000A, F=18kN	190			1.36	V
Q _{rr}	Recovery charge	I _{FM} =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V	190		1900		μC
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 18.0kN				0.028	°C /W
R _{th(c-h)}	Thermal resistance case to heat sink					0.0075	
F _m	Mounting force			10		20	kN
T _{stg}	Stored temperature			-40		190	°C
W _t	Weight				320		g


Fig.1

Fig.2

Fig.3

Fig.4

Fig.5

Fig.6


Fig.7

Fig.8
Outline:
